Atomic Layer Deposited Metal Oxide Bilayers for Metal-Insulator-Semiconductor Photovoltaics – Supplemental Information

Fig. 1: Schottky barrier heights of various diode configurations as measured by Mott-Schottky analysis. The error bars represent the sample standard deviations.

Fig. 2: Representative room temperature current-voltage curves from a) p-type and b) n-type Si diodes utilizing tunnel insulators comprising either AlOₓ or LaOₓ/AlOₓ stacks with similar total thickness.
References


